

ABSTRACT

A technique for attaining a large capacity of a memory card type semiconductor device is disclosed. A Cu pattern is formed centrally of a bending portion (BAL) on a flexible substrate and Cu patterns are formed at end portions of mounting areas (MAL, MAC) located on both sides of the bending portion. When the flexible substrate is bent along the bending portion (BAL), only film exposed portions present on both sides of the Cu pattern are bent with a small radius of curvature and the end portions of the mounting areas (MAL, MAC) and the vicinities thereof are kept flat.